



# PSMN4R1-60YL

N-channel 60 V, 4.1 mΩ logic level MOSFET in LFAK56

20 October 2016

Product data sheet

## 1. General description

Logic level N-channel MOSFET in an LFAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

## 2. Features and benefits

- Advanced TrenchMOS provides low  $R_{DS(on)}$  and low gate charge
- Logic level gate operation
- Avalanche rated, 100% tested
- LFAK provides maximum power density in a Power SO8 package

## 3. Applications

- Synchronous rectifier in LLC topology
- Chargers & adaptors with  $V_{out} < 10$  V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

## 4. Quick reference data

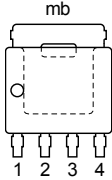
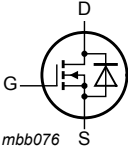
Table 1. Quick reference data

| Symbol                         | Parameter                        | Conditions                                                                                                                                      |     | Min | Typ  | Max | Unit |
|--------------------------------|----------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------|-----|------|
| $V_{DS}$                       | drain-source voltage             | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                                                                                      |     | -   | -    | 60  | V    |
| $I_D$                          | drain current                    | $V_{GS} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                                                                        | [1] | -   | -    | 100 | A    |
| $P_{tot}$                      | total power dissipation          | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                                                                                |     | -   | -    | 238 | W    |
| <b>Static characteristics</b>  |                                  |                                                                                                                                                 |     |     |      |     |      |
| $R_{DS(on)}$                   | drain-source on-state resistance | $V_{GS} = 5\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>                                                    |     | -   | 3.3  | 4.8 | mΩ   |
| <b>Dynamic characteristics</b> |                                  |                                                                                                                                                 |     |     |      |     |      |
| $Q_{GD}$                       | gate-drain charge                | $I_D = 25\text{ A}$ ; $V_{DS} = 48\text{ V}$ ; $V_{GS} = 5\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> |     | -   | 18.1 | -   | nC   |

[1] Continuous current is limited by package.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                                         | Graphic symbol                                                                      |
|-----|--------|-----------------------------------|----------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | S      | source                            |  <p><b>LPAK56; Power-SO8 (SOT669)</b></p> |  |
| 2   | S      | source                            |                                                                                                                            |                                                                                     |
| 3   | S      | source                            |                                                                                                                            |                                                                                     |
| 4   | G      | gate                              |                                                                                                                            |                                                                                     |
| mb  | D      | mounting base; connected to drain |                                                                                                                            |                                                                                     |

## 6. Ordering information

Table 3. Ordering information

| Type number  | Package           |                                                                           |         |
|--------------|-------------------|---------------------------------------------------------------------------|---------|
|              | Name              | Description                                                               | Version |
| PSMN4R1-60YL | LPAK56; Power-SO8 | Plastic single-ended surface-mounted package (LPAK56; Power-SO8); 4 leads | SOT669  |

## 7. Limiting values

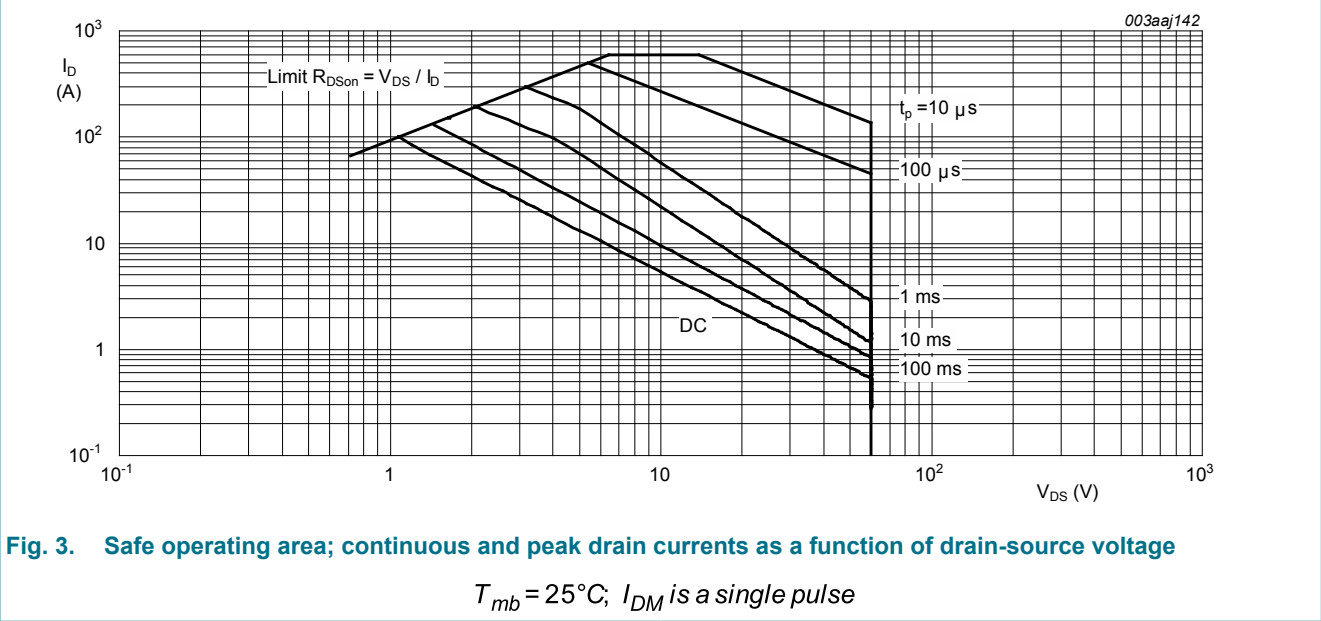
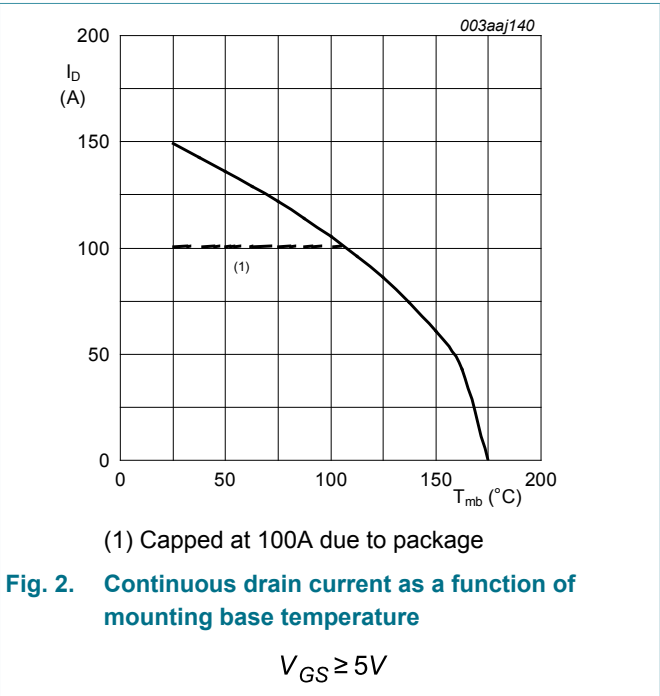
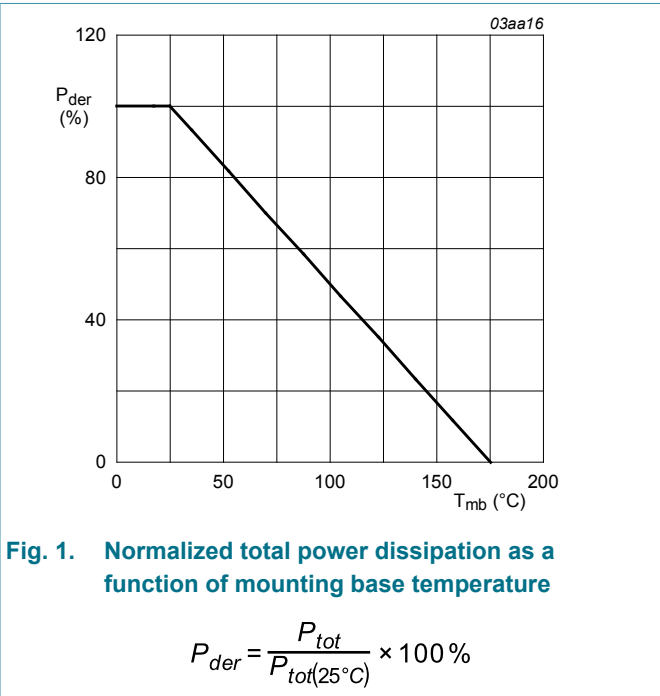
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                    | Parameter               | Conditions                                                                  |     | Min | Max | Unit |
|---------------------------|-------------------------|-----------------------------------------------------------------------------|-----|-----|-----|------|
| $V_{DS}$                  | drain-source voltage    | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                  |     | -   | 60  | V    |
| $V_{DGR}$                 | drain-gate voltage      | $R_{GS} = 20\text{ k}\Omega$                                                |     | -   | 60  | V    |
| $V_{GS}$                  | gate-source voltage     |                                                                             |     | -20 | 20  | V    |
| $P_{tot}$                 | total power dissipation | $T_{mb} = 25\text{ °C}$ ; Fig. 1                                            |     | -   | 238 | W    |
| $I_D$                     | drain current           | $V_{GS} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 2                    | [1] | -   | 100 | A    |
|                           |                         | $V_{GS} = 5\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; Fig. 2                   | [1] | -   | 100 | A    |
| $I_{DM}$                  | peak drain current      | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 3 |     | -   | 593 | A    |
| $T_{stg}$                 | storage temperature     |                                                                             |     | -55 | 175 | °C   |
| $T_j$                     | junction temperature    |                                                                             |     | -55 | 175 | °C   |
| <b>Source-drain diode</b> |                         |                                                                             |     |     |     |      |
| $I_S$                     | source current          | $T_{mb} = 25\text{ °C}$                                                     | [1] | -   | 100 | A    |
| $I_{SM}$                  | peak source current     | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$          |     | -   | 593 | A    |

| Symbol               | Parameter                                    | Conditions                                                                                                                                                                                   |                                         | Min | Max | Unit |
|----------------------|----------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------|-----|-----|------|
| Avalanche ruggedness |                                              |                                                                                                                                                                                              |                                         |     |     |      |
| $E_{DS(AL)S}$        | non-repetitive drain-source avalanche energy | $I_D = 100\text{ A}$ ; $V_{sup} \leq 60\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ;<br>$V_{GS} = 5\text{ V}$ ; $T_{j(init)} = 25\text{ }^\circ\text{C}$ ; unclamped;<br><a href="#">Fig. 4</a> | <a href="#">[2]</a> <a href="#">[3]</a> | -   | 199 | mJ   |

- [1] Continuous current is limited by package.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.



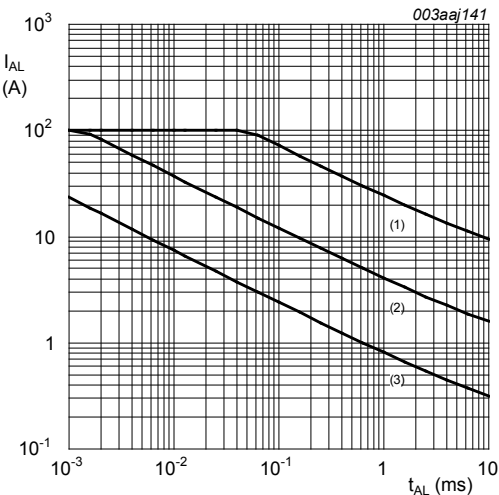


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1)  $T_j(\text{init}) = 25^{\circ}\text{C}$ ; (2)  $T_j(\text{init}) = 150^{\circ}\text{C}$ ; (3) Repetitive Avalanche

8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol                | Parameter                                         | Conditions | Min | Typ | Max  | Unit |
|-----------------------|---------------------------------------------------|------------|-----|-----|------|------|
| $R_{\text{th(j-mb)}}$ | thermal resistance from junction to mounting base | Fig. 5     | -   | -   | 0.63 | K/W  |

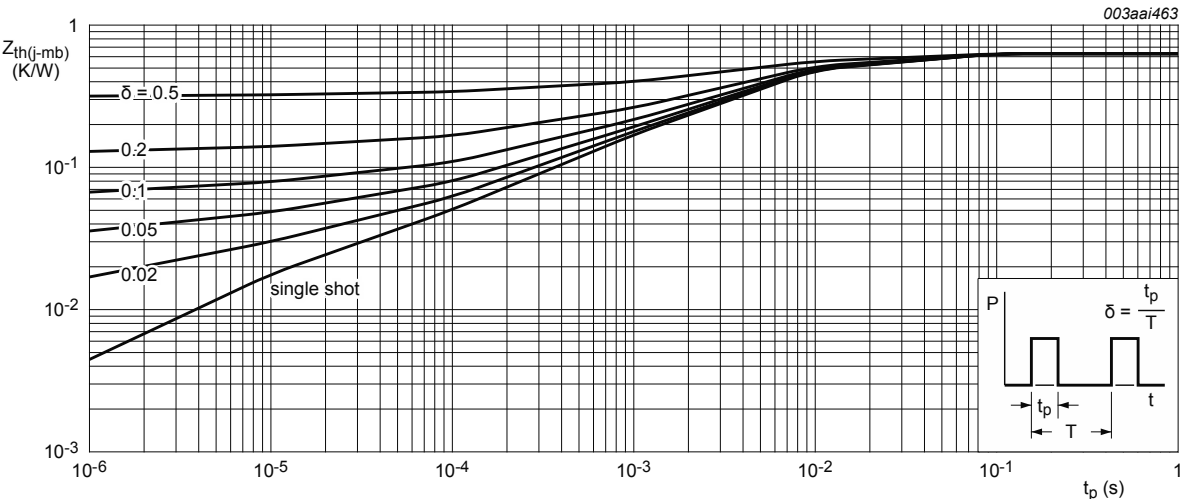


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 9. Characteristics

Table 6. Characteristics

| Symbol                  | Parameter                        | Conditions                                                                                                                                       |  | Min | Typ  | Max  | Unit |
|-------------------------|----------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------|--|-----|------|------|------|
| Static characteristics  |                                  |                                                                                                                                                  |  |     |      |      |      |
| V <sub>(BR)DSS</sub>    | drain-source breakdown voltage   | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                           |  | 60  | -    | -    | V    |
|                         |                                  | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C                                                                          |  | 54  | -    | -    | V    |
| V <sub>GS(th)</sub>     | gate-source threshold voltage    | I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>               |  | 1.4 | 1.7  | 2.1  | V    |
|                         |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <a href="#">Fig. 9</a>                                        |  | -   | -    | 2.45 | V    |
|                         |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <a href="#">Fig. 9</a>                                        |  | 0.5 | -    | -    | V    |
| I <sub>DSS</sub>        | drain leakage current            | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C                                                                           |  | -   | -    | 500  | μA   |
|                         |                                  | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                            |  | -   | 0.12 | 10   | μA   |
| I <sub>GSS</sub>        | gate leakage current             | V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                            |  | -   | 2    | 100  | nA   |
|                         |                                  | V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                                           |  | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>                                                    |  | -   | 3.3  | 4.8  | mΩ   |
|                         |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>                                                   |  | -   | 2.9  | 4.1  | mΩ   |
|                         |                                  | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <a href="#">Fig. 11</a> ; <a href="#">Fig. 12</a>                         |  | -   | -    | 10.8 | mΩ   |
| Dynamic characteristics |                                  |                                                                                                                                                  |  |     |      |      |      |
| Q <sub>G(tot)</sub>     | total gate charge                | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> |  | -   | 103  | -    | nC   |
|                         |                                  | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 5 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>  |  | -   | 54.8 | -    | nC   |
| Q <sub>GS</sub>         | gate-source charge               | T <sub>j</sub> = 25 °C; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>                                                                        |  | -   | 13.6 | -    | nC   |
| Q <sub>GD</sub>         | gate-drain charge                |                                                                                                                                                  |  | -   | 18.1 | -    | nC   |
| C <sub>iss</sub>        | input capacitance                | V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a>                                        |  | -   | 5890 | 7853 | pF   |
| C <sub>oss</sub>        | output capacitance               |                                                                                                                                                  |  | -   | 506  | 607  | pF   |
| C <sub>rss</sub>        | reverse transfer capacitance     |                                                                                                                                                  |  | -   | 276  | 378  | pF   |
| t <sub>d(on)</sub>      | turn-on delay time               | V <sub>DS</sub> = 45 V; R <sub>L</sub> = 1.8 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C                         |  | -   | 28   | -    | ns   |
| t <sub>r</sub>          | rise time                        |                                                                                                                                                  |  | -   | 53   | -    | ns   |
| t <sub>d(off)</sub>     | turn-off delay time              |                                                                                                                                                  |  | -   | 80   | -    | ns   |
| t <sub>f</sub>          | fall time                        |                                                                                                                                                  |  | -   | 47   | -    | ns   |
| Source-drain diode      |                                  |                                                                                                                                                  |  |     |      |      |      |
| V <sub>SD</sub>         | source-drain voltage             | I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 16</a>                                                    |  | -   | 0.78 | 1.2  | V    |

| Symbol   | Parameter             | Conditions                                                                            | Min | Typ | Max | Unit |
|----------|-----------------------|---------------------------------------------------------------------------------------|-----|-----|-----|------|
| $t_{rr}$ | reverse recovery time | $I_S = 20\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; | -   | 29  | -   | ns   |
| $Q_r$    | recovered charge      | $V_{DS} = 25\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$                           | -   | 28  | -   | nC   |

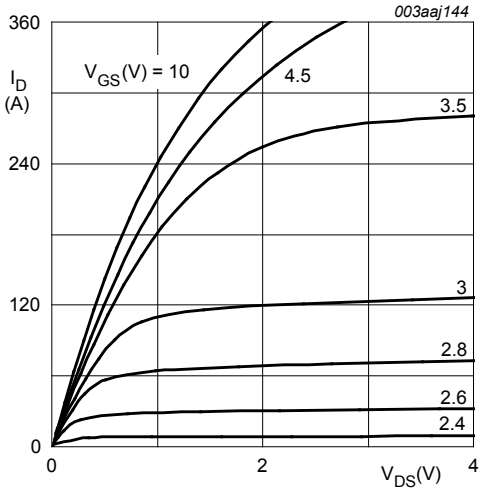


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

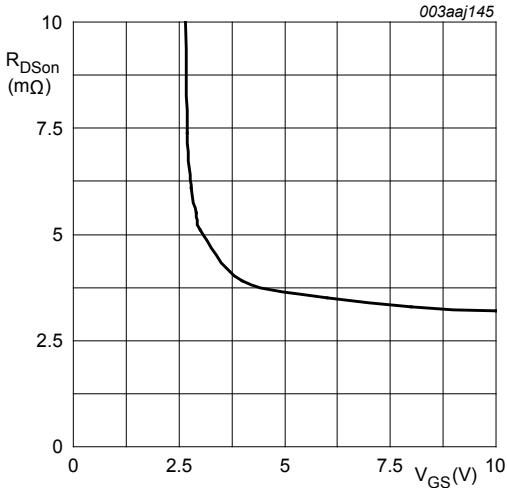


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

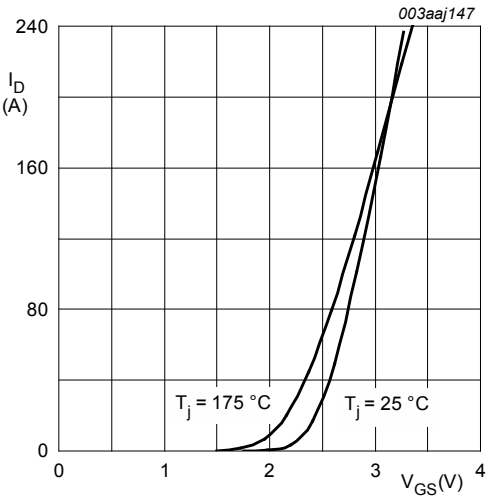


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

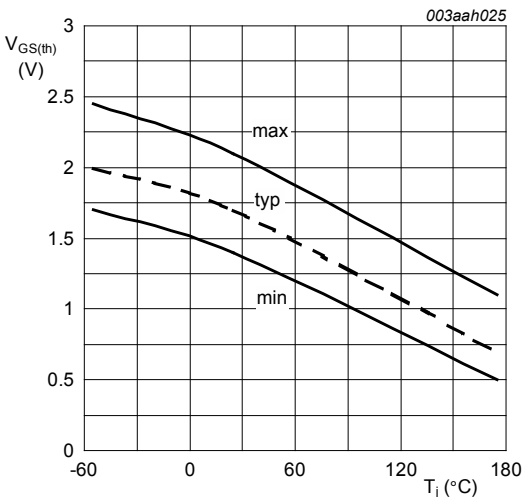


Fig. 9. Gate-source threshold voltage as a function of junction temperature

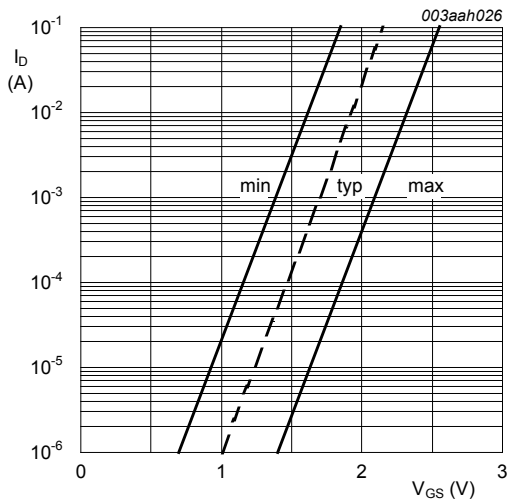


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^{\circ}\text{C}; V_{DS} = 5\text{V}$

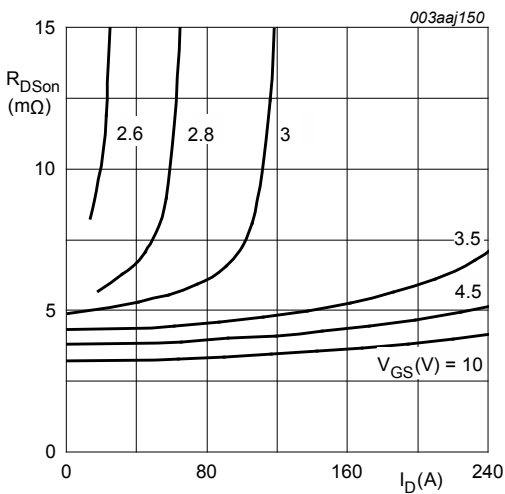


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25^{\circ}\text{C}; t_p = 300\text{ }\mu\text{s}$

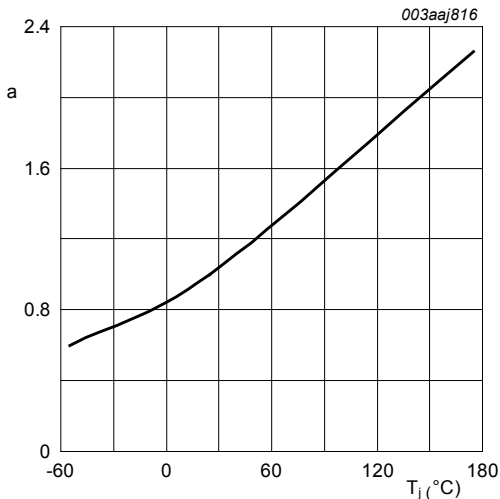


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

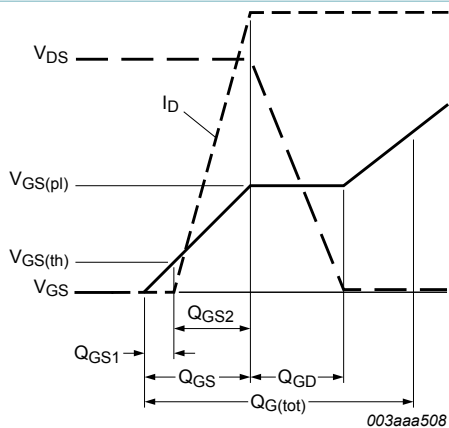


Fig. 13. Gate charge waveform definitions

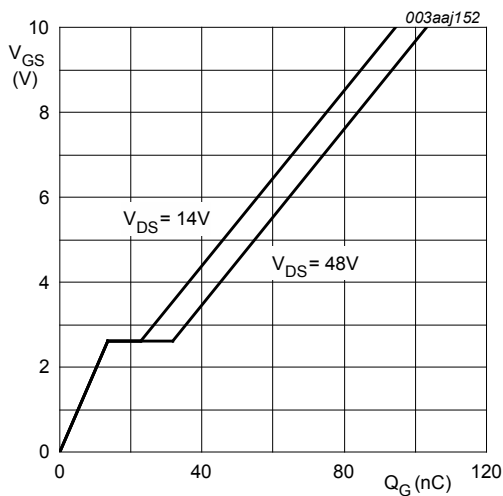


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^{\circ}C$ ;  $I_D = 25A$

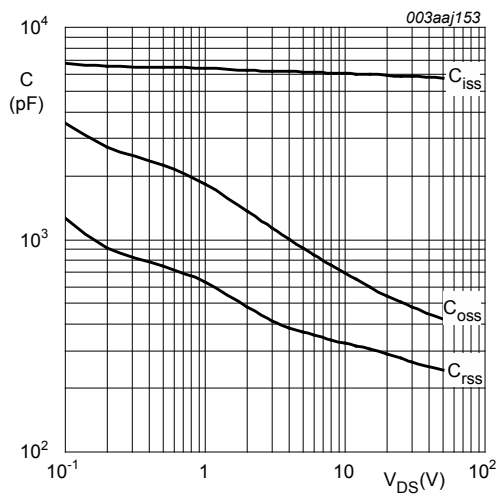


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$T_j = 25^{\circ}C$ ;  $I_D = 25A$

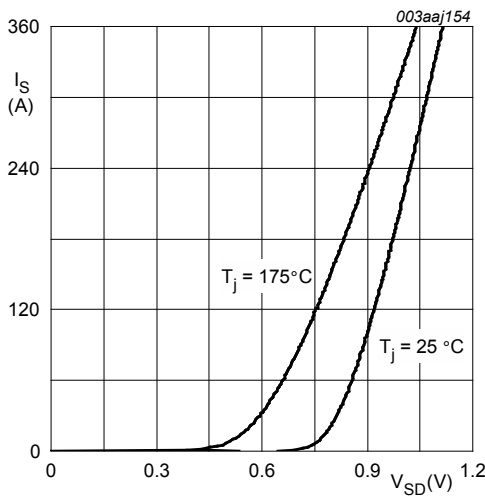


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0V$



10. Package outline

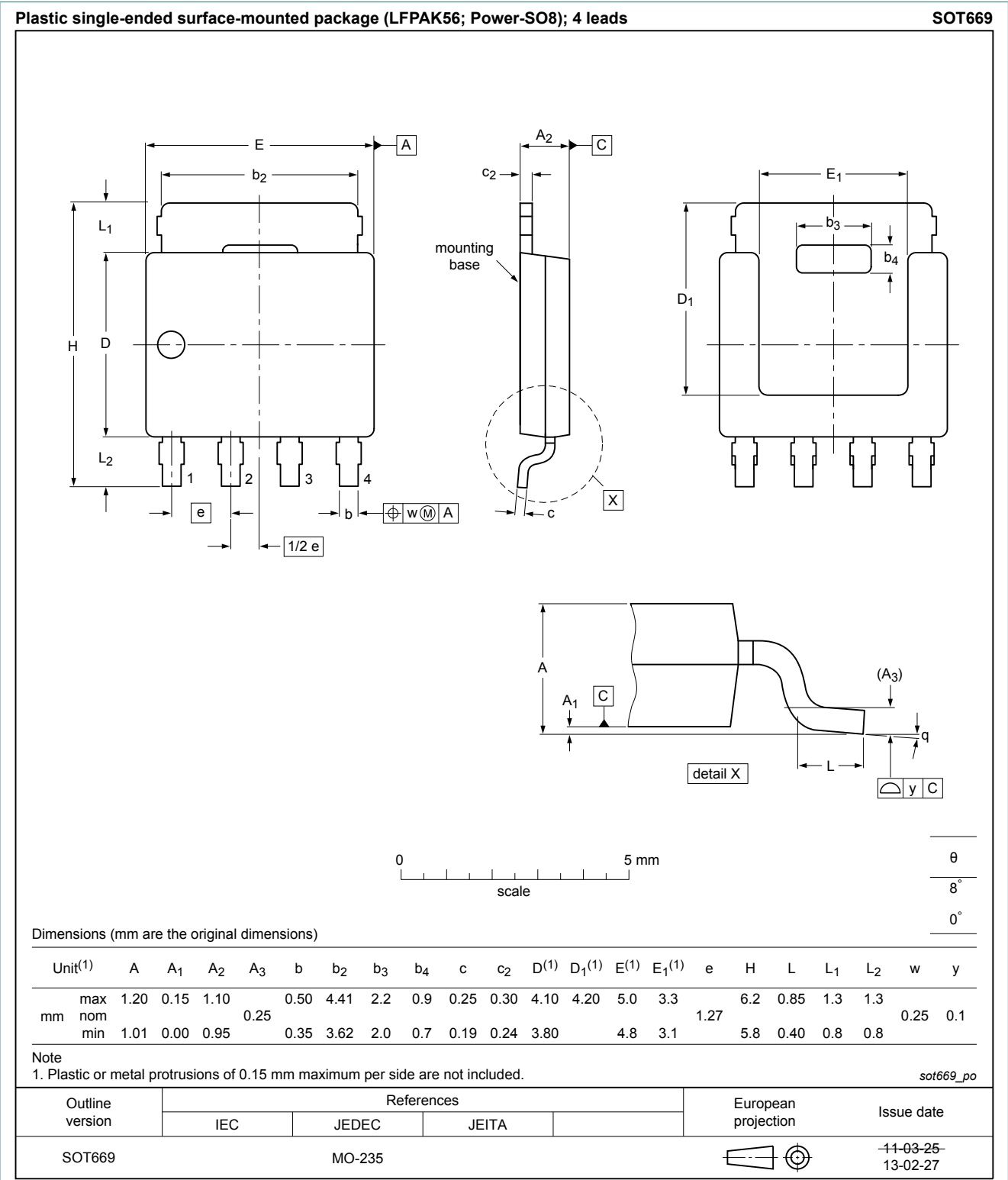


Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

## 11. Legal information

### 11.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
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12. Contents

1 General description ..... 1

2 Features and benefits ..... 1

3 Applications ..... 1

4 Quick reference data ..... 1

5 Pinning information ..... 2

6 Ordering information ..... 2

7 Limiting values ..... 2

8 Thermal characteristics ..... 4

9 Characteristics ..... 5

10 Package outline ..... 9

11 Legal information ..... 10

11.1 Data sheet status ..... 10

11.2 Definitions ..... 10

11.3 Disclaimers ..... 10

11.4 Trademarks ..... 11

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Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



## JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,  
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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